



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 40V
- I_D 155A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 2.5mohm
- 100% EAS Tested
- 100% VDS Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- U

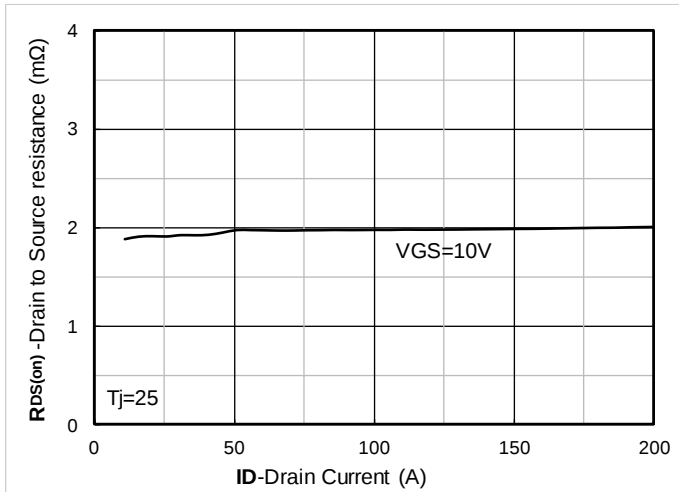


Figure7. $R_{DS(on)}$ VS Drain Current

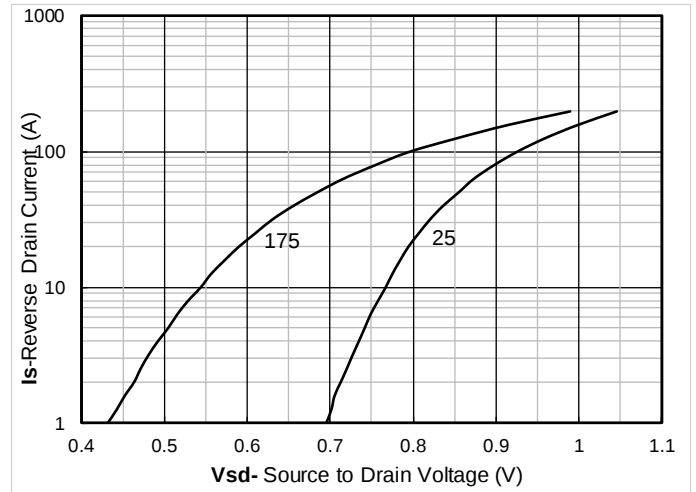


Figure8. Forward characteristics of reverse diode

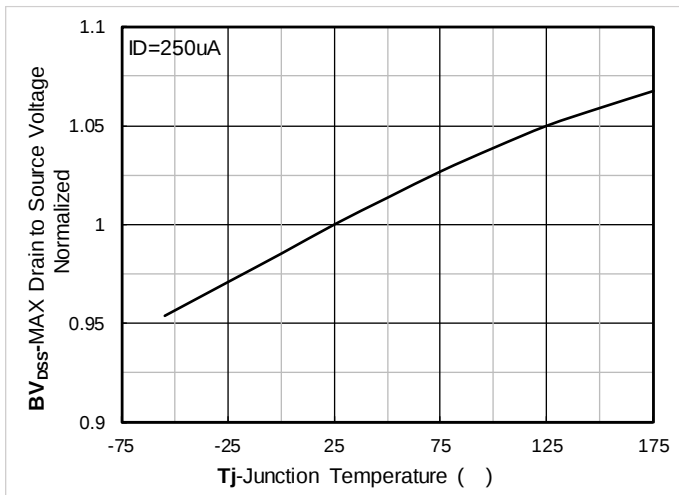


Figure9. Normalized breakdown voltage

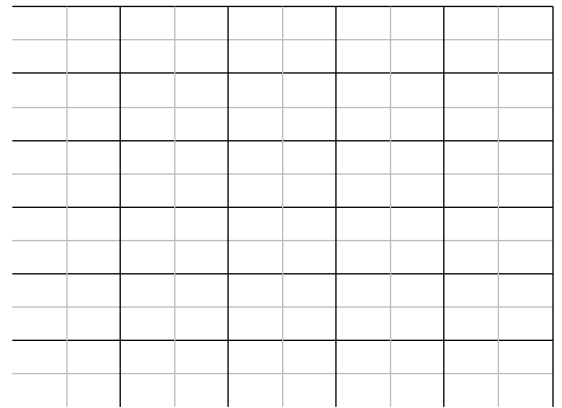


Figure10. Normalized Threshold voltage

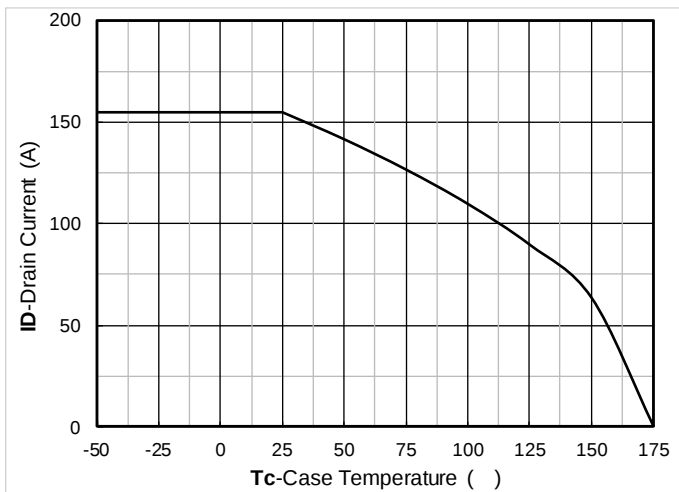


Figure11. Current dissipation

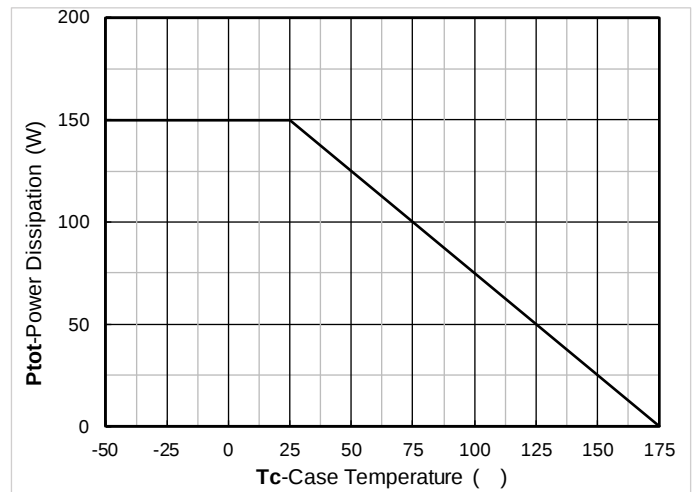


Figure12. Power dissipation



■ TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		



Disclaimer

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